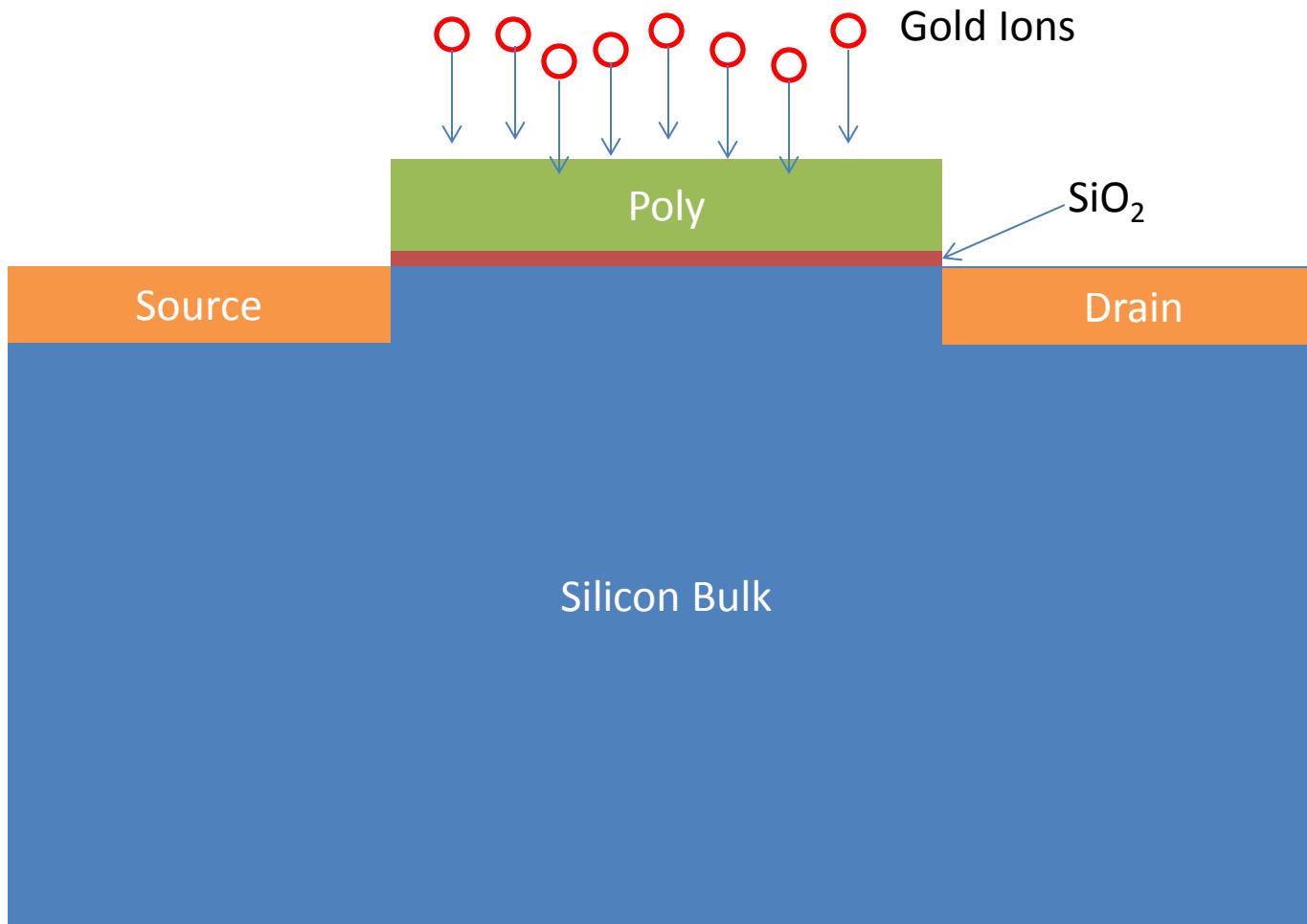


Introduction to

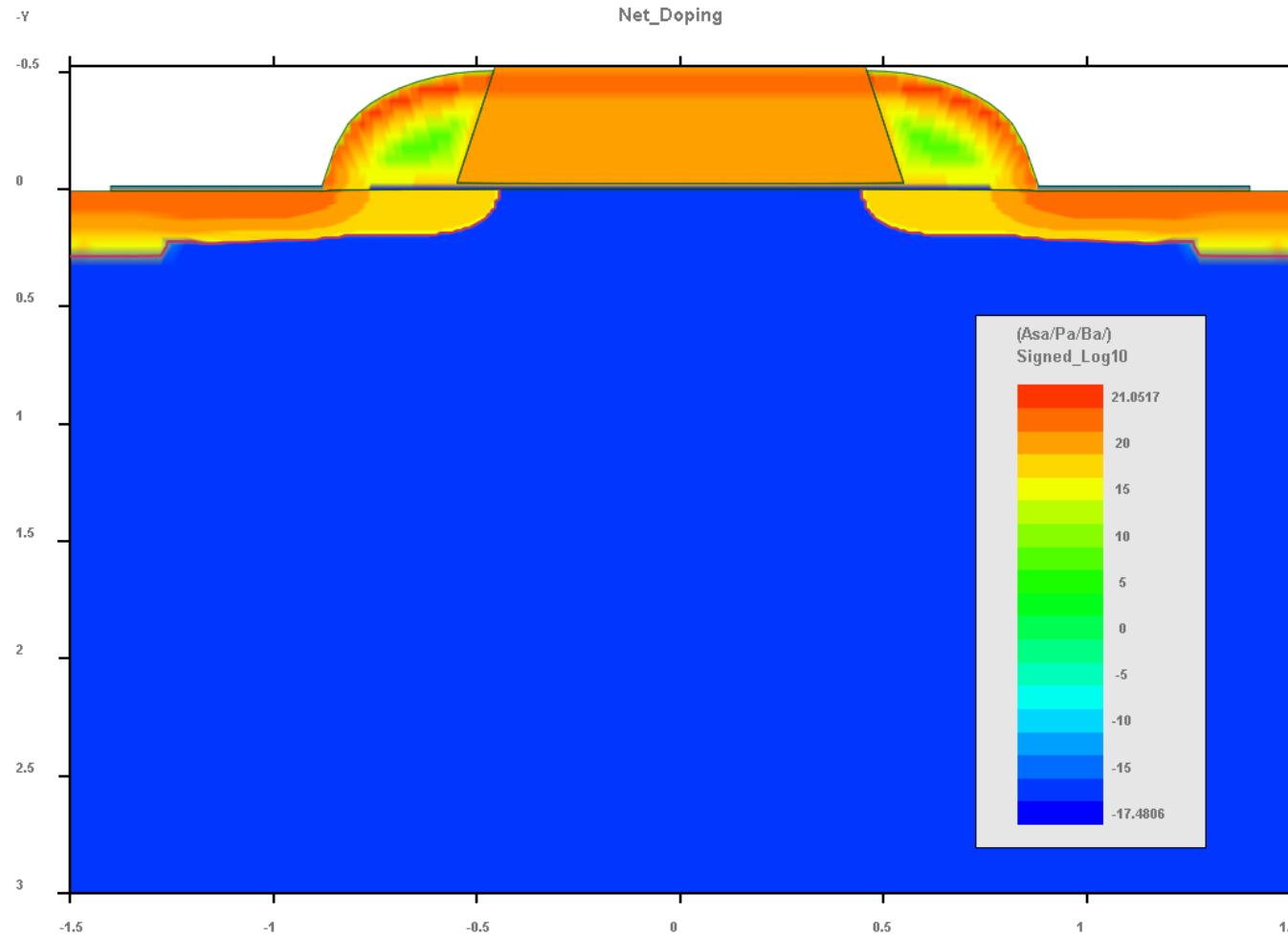
Heavy Ion Radiation Simulation



Heavy Ion Radiation

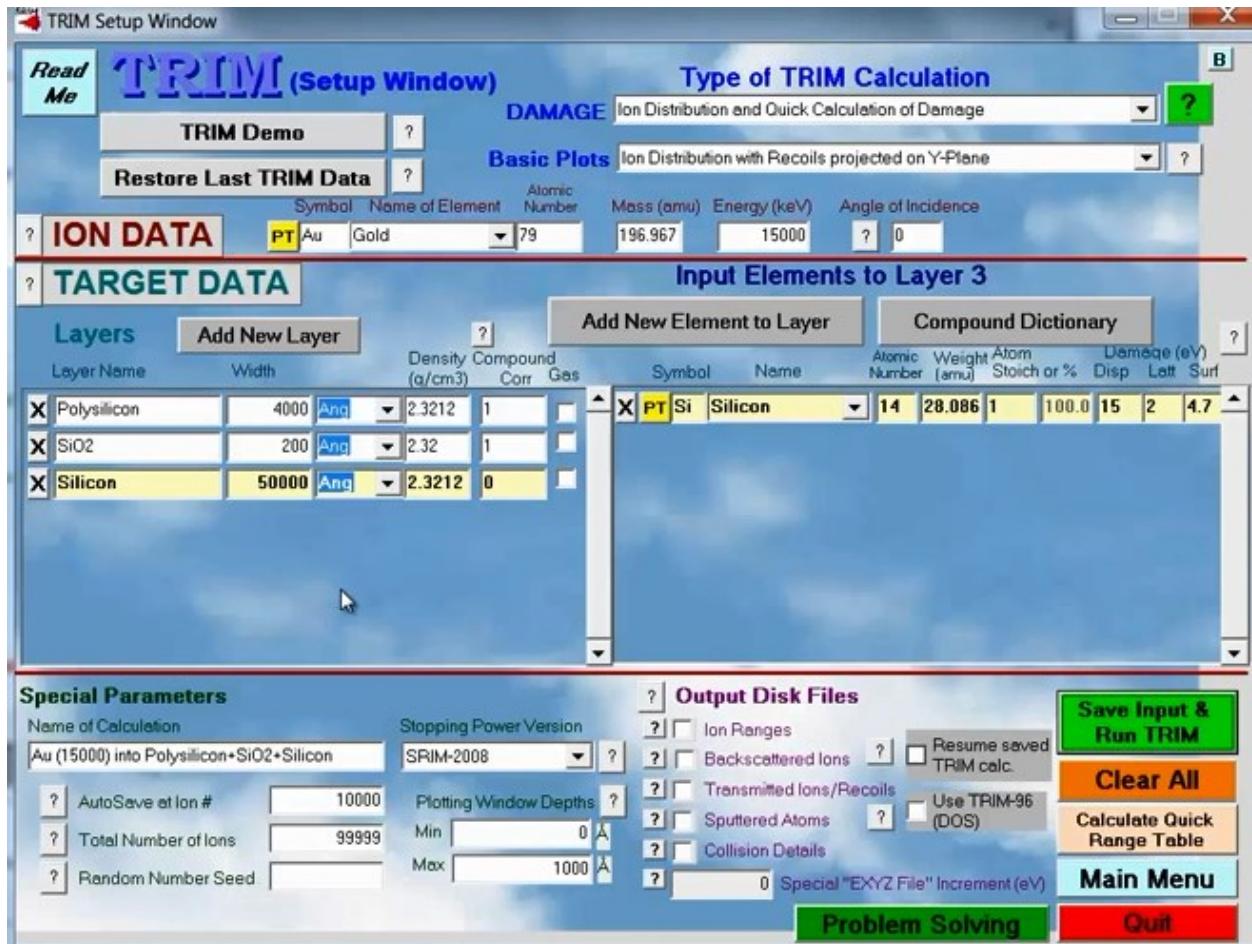


Simulated Structure



NovaTCAD

Monte-Carlo Simulation with TRIM



- Monte-Carlo simulation is performed by using TRIM.
- Gold with energy of 1.6 MeV is used to penetrate through Polysilicon/SiO₂/Silicon layers

This software can be found at www.srim.org

The Monte-Carlo Simulation Results

```
$ use $ or # as first character for comment lines
$===== Au (15000) into Poly Silicon+SiO2 - quar =====
$      SRIM-2013.00
$=====
$      Ion and Recoil IONIZATION
$ See SRIM Outputs\TDATA.txt for details
$=====
$-----
$      Recoil/Damage Calculations made with Kinchin-Pease Estimates
$-----
$ See file : SRIM Outputs\TDATA.txt for calculation data
$ Ion = Au Energy = 15000 keV
$=====
$===== TARGET MATERIAL =====
$Layer 1 : Poly Silicon
$Layer Width = 40000.E-01 A ;
$ Layer # 1- Density = 4.976E22 atoms/cm3 = 2.321 g/cm3
$ Layer # 1- Si = 100 Atomic Percent = 100 Mass Percent
$Layer 2 : SiO2 - quartz (ICRU-245)
$Layer Width = 20000.E-02 A ;
$ Layer # 2- Density = 6.975E22 atoms/cm3 = 2.32 g/cm3
$ Layer # 2- O = 66.6 Atomic Percent = 53.2 Mass Percent
$ Layer # 2- Si = 33.3 Atomic Percent = 46.7 Mass Percent
$Layer 3 : Silicon
$Layer Width = 50000.E+00 A ;
$ Layer # 3- Density = 4.976E22 atoms/cm3 = 2.321 g/cm3
$ Layer # 3- Si = 100 Atomic Percent = 100 Mass Percent
$=====
$ Total Ions calculated =002000.00
$=====
$ Ionization Energy Units are >>> eV /(Angstrom-Ion) <<<
$=====
$ TARGET    IONIZ.   IONIZ.
$ DEPTH     by       by
$ (Ang)     IONS     RECOILS
$-----
542010.E-03 3195.60E-01 5244.93E-02
108401.E-02 3175.20E-01 5191.39E-02
.....
596201.E-02 3049.19E-01 6074.16E-02
542000.E-01 0000.00E+00 0000.00E+00
```

- The simulation results will be saved to a text file named as trim_ioniz.txt
- The file is to be used by APSYS for device simulation

APSYS Device Simulation

- Two ion strikes with some time delays in between are defined in the APSYS .sol file.
- Monte Carlo simulation results (trim_ioniz.txt) is used as the input data for the Linear Energy Transfer (LET)

```
$ 1st ion strikes
radiation_heavy_ion let_file=trim_ioniz.txt let_unit=eV/angstrom &&
depth_unit=angstrom layer1_material=Si layer2_material=SiO2 &&
layer3_material=Si &&
lateral_straggle=0.2 location_xz=(0 0) &&
layer1_from_top=0.5 layer2_from_top=0.025 layer3_from_top=10 &&
pulse_fwhm=1.5e-12

$ 2nd ion strikes
radiation_heavy_ion let_file=trim_ioniz.txt let_unit=eV/angstrom &&
depth_unit=angstrom layer1_material=Si layer2_material=SiO2 &&
layer3_material=Si &&
lateral_straggle=0.2 location_xz=(0.2 0) &&
layer1_from_top=0.5 layer2_from_top=0.025 layer3_from_top=10 &&
pulse_fwhm=1.5e-12
```

APSYS Device Simulation

- The drain voltage is first scanned to 5V with source/gate terminals grounded
- Light is used to control the radiation generation rate
- A Gaussian function is used to define each pulse. Parameters are defined for the two pulses with the second strike having a 2 picosecond delay
- After the strike, wait for 1 nanosecond to observe the recovery

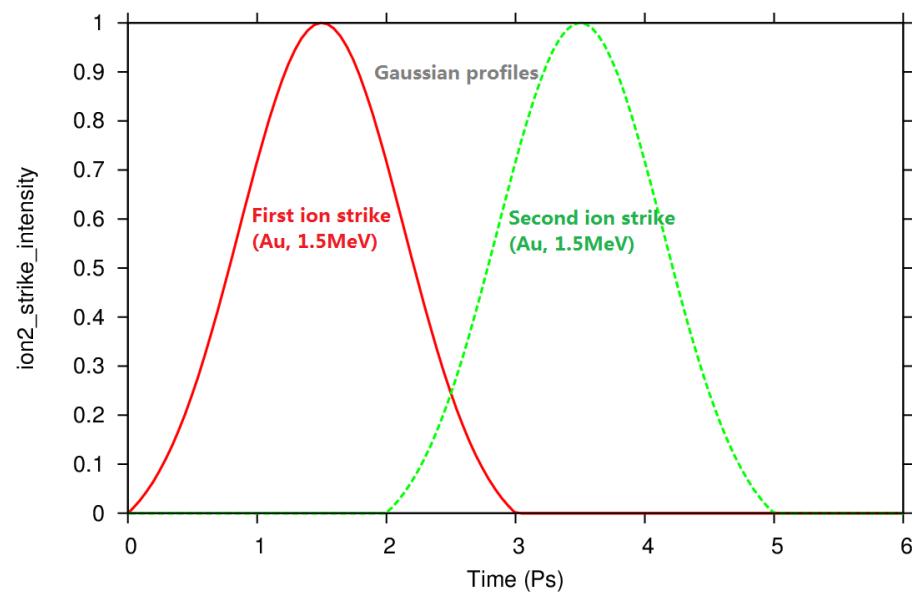
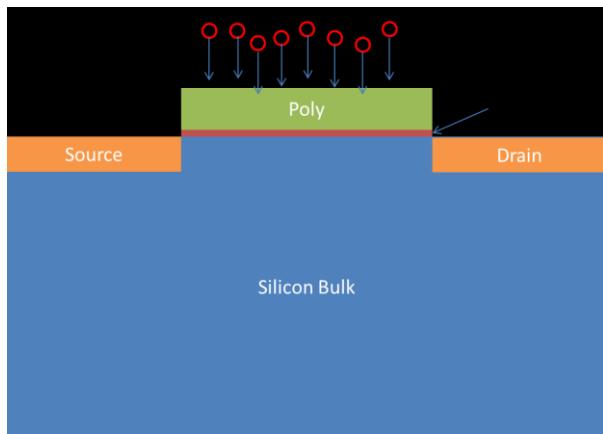
```
$ scan #3
scan var=time value_to=6.e-12 &&
var2=light  function_label2=gaus_pulse1 &&
var3=light2  function_label3=gaus_pulse2 &&
init_step=0.1e-12 max_step=0.2e-12

scan_function label=gaus_pulse1 type=gaussian &&
gsn_t1=0.  gsn_dt=1.5e-12 gsn_s1=0.  gsn_s2=1.

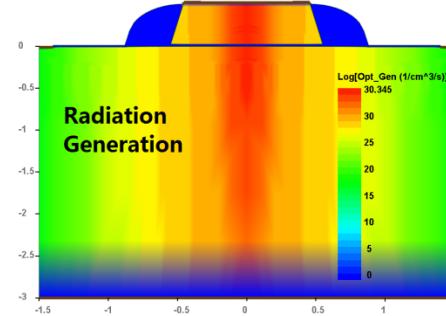
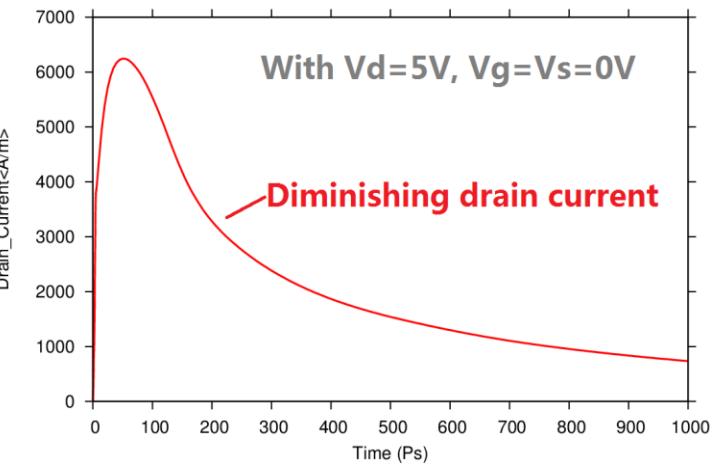
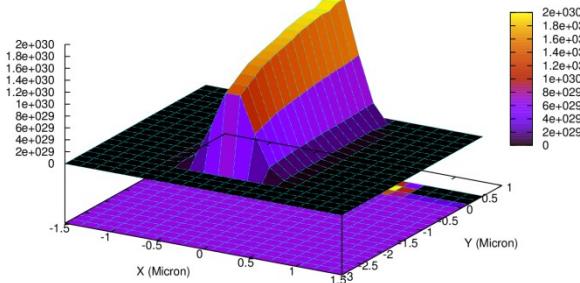
scan_function label=gaus_pulse2 type=gaussian &&
gsn_t1=2.e-12  gsn_dt=1.5e-12 gsn_s1=0.  gsn_s2=1.

$ scan #4
scan var=time value_to=1000.e-12 &&
init_step=0.1e-12 max_step=50.e-12 min_step=0.001e-12 &&
var2=light  value2_to=0.0  &&
var3=light2  value3_to=0.
```

Heavy-ion Radiation Summary



Radiation Generation



NovaTCAD

Crosslight Customer Locations



Over 300 customers located around the world



*A Canadian company with 20 years of history
The world's first commercial TCAD for laser diode*



*The world's No.1 provider of optics and photonics TCAD
The world's most advanced stacked planes 3D TCAD*

